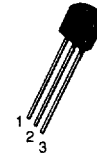
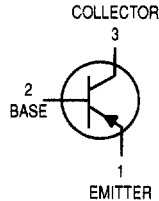


Amplifier Transistor

PNP Silicon

2N4125



CASE 29-04, STYLE 1
TO-92 (TO-226AA)

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	30	Vdc
Collector-Base Voltage	V_{CBO}	30	Vdc
Emitter-Base Voltage	V_{EBO}	4.0	Vdc
Collector Current — Continuous	I_C	200	mAdc
Total Device Dissipation @ $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	625 5.0	mW mW/ $^\circ\text{C}$
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	1.5 12	Watts mW/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	200	$^\circ\text{C/W}$
Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	$^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
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OFF CHARACTERISTICS

Collector-Emitter Breakdown Voltage ⁽¹⁾ ($I_C = 1.0$ mAdc, $I_B = 0$)	$V_{(BR)CEO}$	30	—	Vdc
Collector-Base Breakdown Voltage ($I_C = 10$ μ Adc, $I_E = 0$)	$V_{(BR)CBO}$	30	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 10$ μ Adc, $I_C = 0$)	$V_{(BR)EBO}$	4.0	—	Vdc
Collector Cutoff Current ($V_{CB} = 20$ Vdc, $I_E = 0$)	I_{CBO}	—	50	nAdc
Emitter Cutoff Current ($V_{EB} = 3.0$ Vdc, $I_C = 0$)	I_{EBO}	—	50	nAdc

1. Pulse Test: Pulse Width ≤ 300 μ s, Duty Cycle = 2.0%.

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted) (Continued)

Characteristic	Symbol	Min	Max	Unit
ON CHARACTERISTICS				
DC Current Gain ⁽¹⁾ ($I_C = 2.0 \text{ mA}$, $V_{CE} = 1.0 \text{ Vdc}$) ($I_C = 50 \text{ mA}$, $V_{CE} = 1.0 \text{ Vdc}$)	h_{FE}	50 25	150 —	—
Collector–Emitter Saturation Voltage ⁽¹⁾ ($I_C = 50 \text{ mA}$, $I_B = 5.0 \text{ mA}$)	$V_{CE(sat)}$	—	0.4	Vdc
Base–Emitter Saturation Voltage ⁽¹⁾ ($I_C = 50 \text{ mA}$, $I_B = 5.0 \text{ mA}$)	$V_{BE(sat)}$	—	0.95	Vdc

SMALL-SIGNAL CHARACTERISTICS

Current–Gain — Bandwidth Product ($I_C = 10 \text{ mA}$, $V_{CE} = 20 \text{ Vdc}$, $f = 100 \text{ MHz}$)	f_T	200	—	MHz
Input Capacitance ($V_{EB} = 0.5 \text{ Vdc}$, $I_C = 0$, $f = 1.0 \text{ MHz}$)	C_{ibo}	—	10	pF
Collector–Base Capacitance ($V_{CB} = 5.0 \text{ Vdc}$, $I_E = 0$, $f = 1.0 \text{ MHz}$)	C_{cb}	—	4.5	pF
Small–Signal Current Gain ($I_C = 2.0 \text{ mA}$, $V_{CE} = 10 \text{ Vdc}$, $f = 1.0 \text{ kHz}$)	h_{fe}	50	200	—
Current Gain — High Frequency ($I_C = 10 \text{ mA}$, $V_{CE} = 20 \text{ Vdc}$, $f = 100 \text{ MHz}$)	$ h_{fe} $	2.0	—	—
Noise Figure ($I_C = 100 \mu\text{A}$, $V_{CE} = 5.0 \text{ Vdc}$, $R_S = 1.0 \text{ k ohm}$, $f = 1.0 \text{ kHz}$)	NF	—	5.0	dB

1. Pulse Test: Pulse Width $\leq 300 \mu\text{s}$, Duty Cycle = 2.0%.

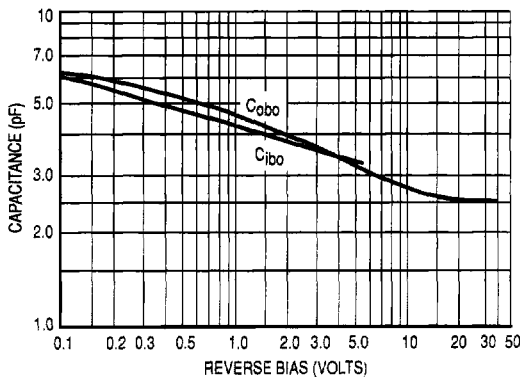


Figure 1. Capacitance

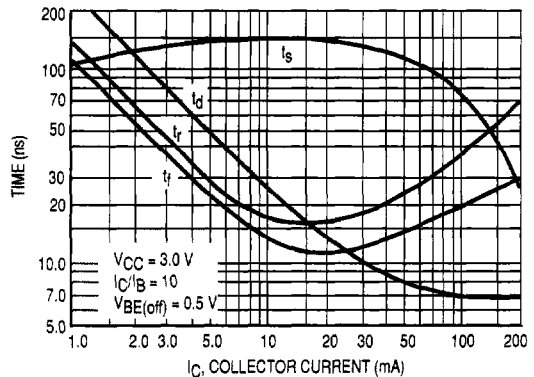


Figure 2. Switching Times

AUDIO SMALL-SIGNAL CHARACTERISTICS

NOISE FIGURE

$V_{CE} = -5.0 \text{ Vdc}$, $T_A = 25^\circ\text{C}$

Bandwidth = 1.0 Hz

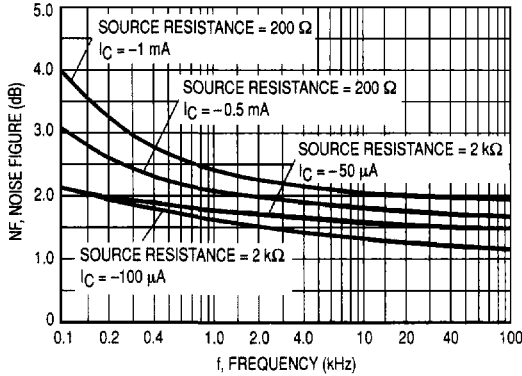


Figure 3. Frequency Variations

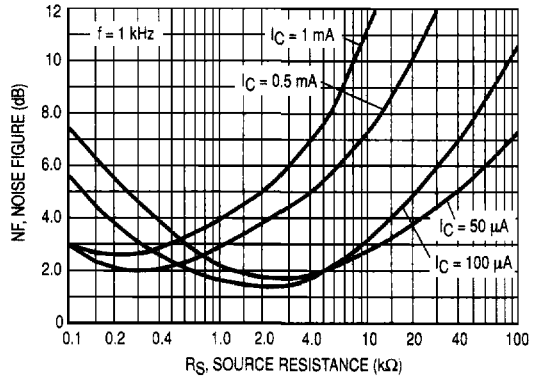


Figure 4. Source Resistance

h PARAMETERS

$V_{CE} = 10 \text{ V}$, $f = 1 \text{ kHz}$, $T_A = 25^\circ\text{C}$

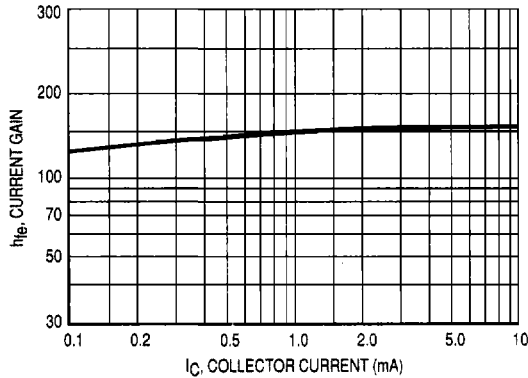


Figure 5. Current Gain

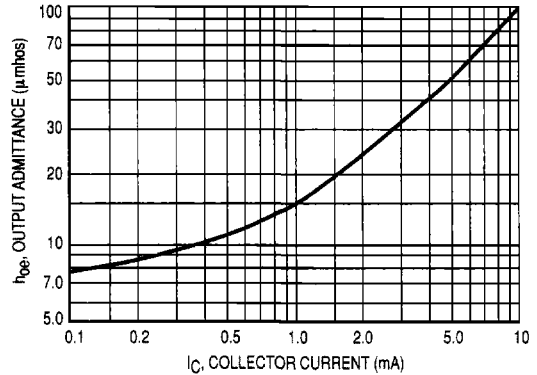


Figure 6. Output Admittance

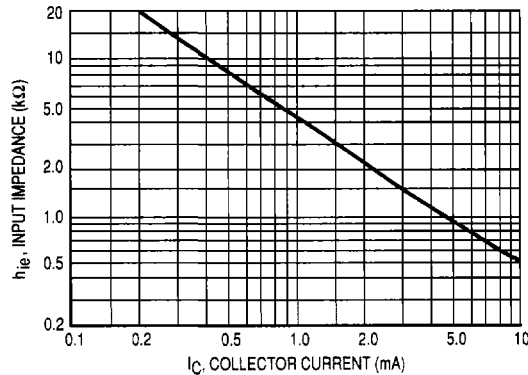


Figure 7. Input Impedance

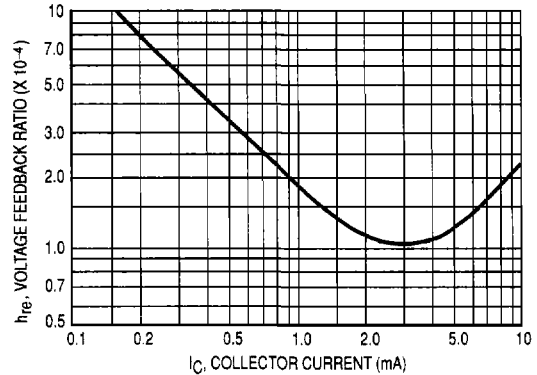


Figure 8. Voltage Feedback Ratio

STATIC CHARACTERISTICS

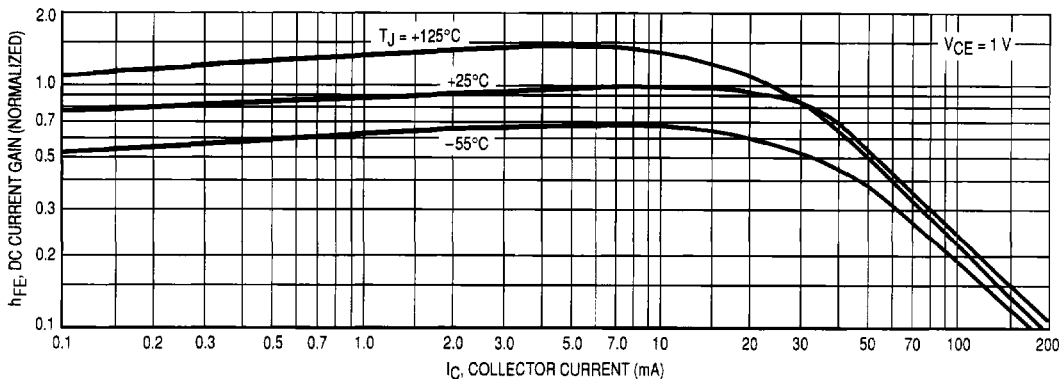


Figure 9. DC Current Gain

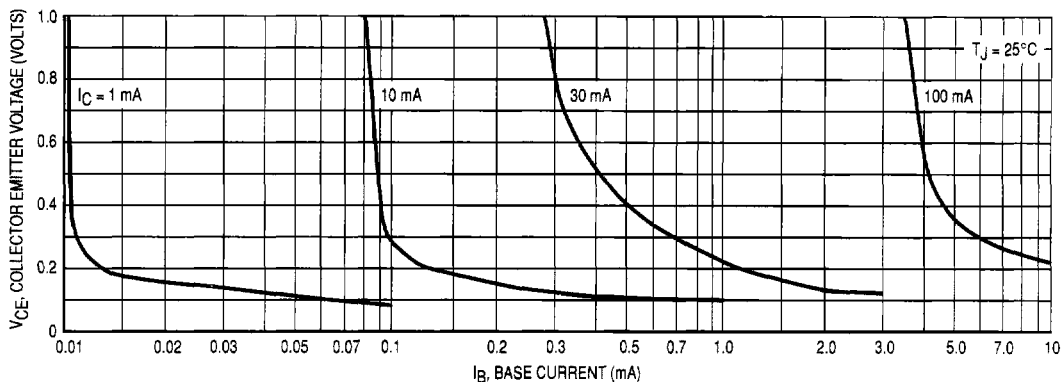


Figure 10. Collector Saturation Region

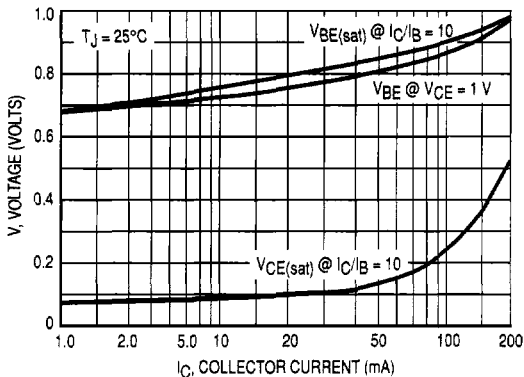


Figure 11. "On" Voltages

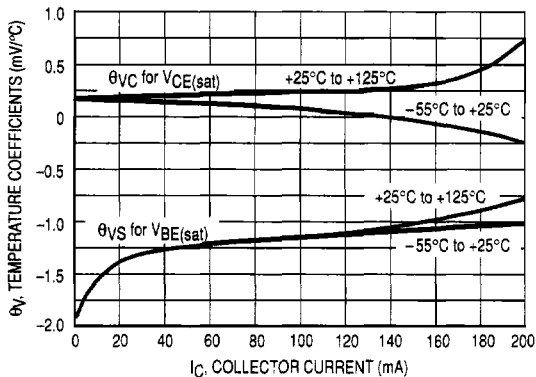


Figure 12. Temperature Coefficients